

FORM PTO-1449				Atty. Docket No.		Appln. No.	
<u>LIST OF DOCUMENTS CITED BY APPLICANT</u>				XA-9967		10/695,798	
				Applicant			
				Atsushi HIRAIWA t al.			
				Filing Date		Group	
				Herewith 10/30/2003		2829B	
<b>U.S. PATENT DOCUMENTS</b>							
Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
<b>FOREIGN PATENT DOCUMENTS</b>							
Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
<i>CME</i>	AH	11-177047	7/2/99	Japan	✓	✓	abstract
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
<b>OTHER (including author, title, date, pertinent pages, etc.)</b>							
<i>CME</i>	AO	Ultra Clean Society closing memorial symposium, "toward the new century led by semiconductor", September 24-25, 2000, pp. 42-52.					
<i>CME</i>	AP	Katsuyuki Sekine et al., IEEE Transactions on Electron Devices, "Highly Reliable Ultrathin Silicon Oxide Film Formation at Low Temperature by Oxygen Radical Generated in High-Density Krypton Plasma", Vol. 48, No. 8, August 2001, pp. 1550-1555.					
<i>CME</i>	AQ	Masaki Hirayama et al., IEEE, "Low-Temperature Growth of High-Integrity Silicon Oxide Films by Oxygen Radical Generated in High-Density Krypton Plasma", 1999, pp. 499-502.					
Examiner				Date Considered			
<i>C. J. Evers</i>				3-10-05			
<b>EXAMINER:</b> Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							